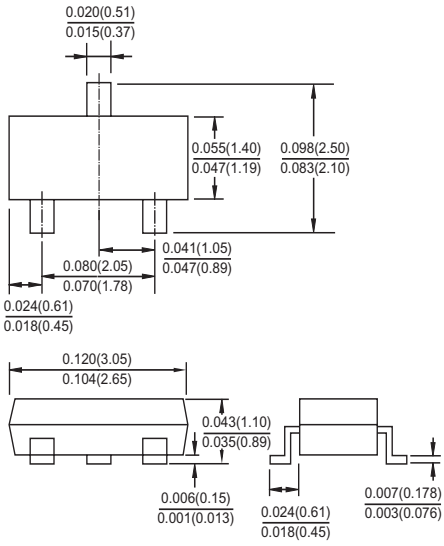
TAIWAN SEMICONDUCTOR

BAS70 / -04 / -05 / -06

200m Watts Surface Mount Schottky Barrier Diode

SOT-23

RoHS COMPLIANCE



Dimensions in inches and (millimeters)

Features

- ✧ Low turn-on voltage
- ✧ Fast switching
- ✧ PN junction guard Ring for transient and ESD protection

Mechanical Data

- ✧ Case: SOT-23, Molded plastic
- ✧ Terminals: Solderable per MIIL-STD-202, Method 208
- ✧ Marking & Polarity: See diagram
- ✧ Weight: 0.008 grams

Maximum Ratings TA=25 °C unless otherwise specified

Type Number	Symbol	BAS70	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	70	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	V
Forward Continuous Current (Note 1)	I_F	70	mA
Non-Repetitive Peak Forward Surge Current @ t ≦1.0s	I_{FSM}	100	mA
Power Dissipation (Note 1)	Pd	200	mW
Thermal Resistance Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625	K/W
Operating Junction Temperature Range	T_J	-55 to + 125	°C
Storage Temperature Range	T_{STG}	-65 to + 150	°C

Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Reverse Breakdown Voltage (Note 2), IR=10uA	$V_{(BR)}$	70		
Reverse Leakage Current tp<300us, VR=50V	I_R	–	100	nA
Forward Voltage Drop tp=300us, IF=1.0mA tp<300us, IF=15mA	V_F	–	410 1000	mV
Junction Capacitance VR=0, f=1.0MHz	Cj	–	2.0	pF
Reverse Recovery Time (Note 3)	trr	–	5.0	nS

Notes: 1. Valid Provided that Terminals are Kept at Ambient Temperature.
2. Test Period < 3000uS.
3. Reverse Recovery Test Conditions: IF=IR=10mA, Irr=1.0mA, RL=100Ω.

Version: C07

RATINGS AND CHARACTERISTIC CURVES (BAS70 / -04 / -05 / -06)

FIG.1- POWER DERATING CURVE

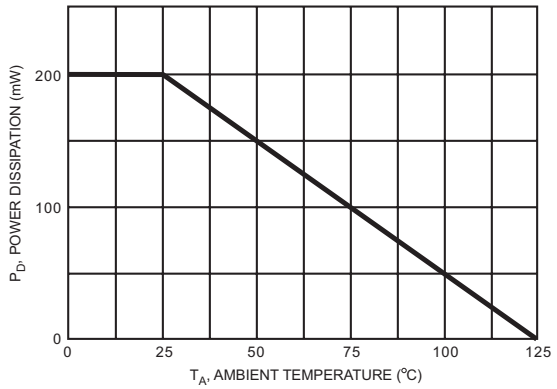


FIG.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PER LEG

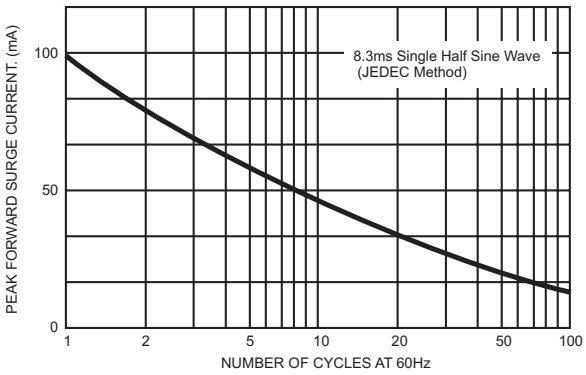


FIG.3- TYPICAL FORWARD CHARACTERISTICS

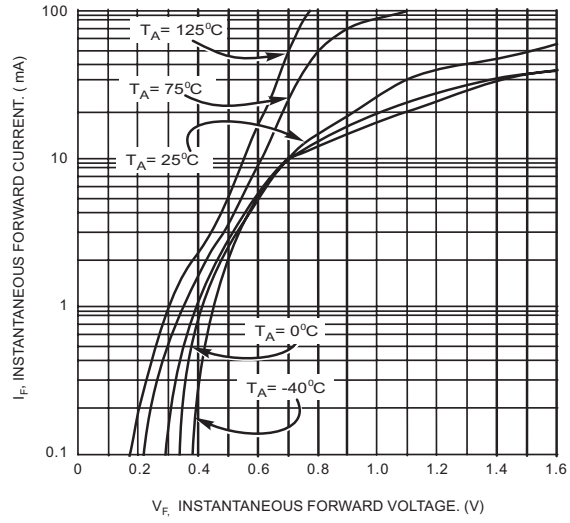


FIG.4- TYPICAL REVERSE CHARACTERISTICS

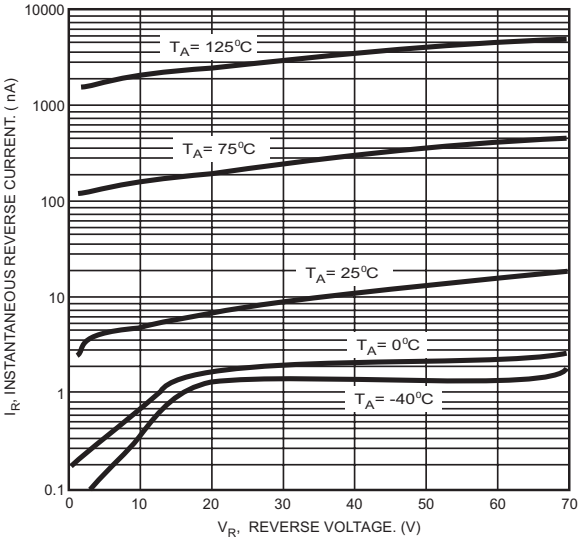


FIG.5- TYPICAL TOTAL CAPACITANCE VS REVERSE VOLTAGE

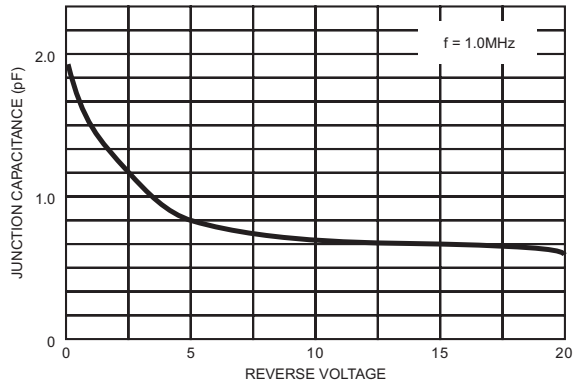


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS